

# MOS FIELD EFFECT TRANSISTOR $\mu$ PA1902

#### N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### **DESCRIPTION**

The  $\mu$ PA1902 is a switching device, which can be driven directly by a 4.5 V power source.

This  $\mu$ PA1902 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power management switch of portable machine and so on.

#### **FEATURES**

- 4.5 V drive available
- Low on-state resistance

RDS(on)1 = 17 m $\Omega$  TYP. (VGS = 10 V, ID = 3.5 A)

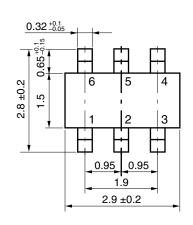
 $R_{DS(on)2} = 22 \text{ m}\Omega \text{ TYP. (Vgs} = 4.5 \text{ V, I}_D = 3.5 \text{ A})$ 

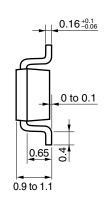
#### ORDERING INFORMATION

| PART NUMBER | PACKAGE                     |  |
|-------------|-----------------------------|--|
| μPA1902TE   | SC-95 (Mini Mold Thin Type) |  |

Marking: TY

#### PACKAGE DRAWING (Unit: mm)



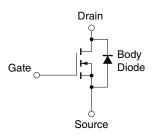


1, 2, 5, 6: Drain 3 : Gate 4 : Source

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ )

| Drain to Source Voltage (V <sub>GS</sub> = 0 V) | VDSS            | 30          | V  |
|---|-----------------|-------------|----|
| Gate to Source Voltage (VDS = 0 V)              | Vgss            | ±20         | V  |
| Drain Current (DC)                              | ID(DC)          | ±7.0        | Α  |
| Drain Current (pulse) Note1                     | ID(pulse)       | ±28         | Α  |
| Total Power Dissipation                         | P <sub>T1</sub> | 0.2         | W  |
| Total Power Dissipation Note2                   | P <sub>T2</sub> | 2.0         | W  |
| Channel Temperature                             | Tch             | 150         | °C |
| Storage Temperature                             | Tstg            | -55 to +150 | °C |

#### **EQUIVALENT CIRCUIT**



- **Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%
  - **2.** Mounted on FR-4 board of 50 mm x 50 mm x 1.6 mm,  $t \le 5$  sec.

**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge. (It does not have built-in G-S protection diode.)

When this product actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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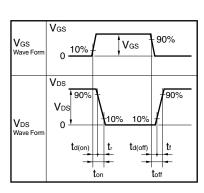


#### **ELECTRICAL CHARACTERISTICS (TA = 25°C)**

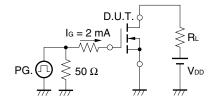
| CHARACTERISTICS                     | SYMBOL               | TEST CONDITIONS                                 | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|---|------|------|------|------|
| Zero Gate Voltage Drain Current     | IDSS                 | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V   |      |      | 1.0  | μΑ   |
| Gate Leakage Current                | Igss                 | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V  |      |      | ±100 | nA   |
| Gate Cut-off Voltage                | V <sub>GS(off)</sub> | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA | 1.5  | 2.0  | 2.5  | V    |
| Forward Transfer Admittance         | yfs                  | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.5 A  | 3.0  |      |      | S    |
| Drain to Source On-state Resistance | R <sub>DS(on)1</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A  |      | 17   | 22   | mΩ   |
|                                     | R <sub>DS(on)2</sub> | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.5 A |      | 22   | 30   | mΩ   |
| Input Capacitance                   | Ciss                 | V <sub>DS</sub> = 10 V                          |      | 780  |      | pF   |
| Output Capacitance                  | Coss                 | V <sub>GS</sub> = 0 V                           |      | 180  |      | pF   |
| Reverse Transfer Capacitance        | Crss                 | f = 1 MHz                                       |      | 120  |      | pF   |
| Turn-on Delay Time                  | t <sub>d(on)</sub>   | V <sub>DD</sub> = 15 V, I <sub>D</sub> = 1.0 A  |      | 16   |      | ns   |
| Rise Time                           | <b>t</b> r           | V <sub>GS</sub> = 10 V                          |      | 10   |      | ns   |
| Turn-off Delay Time                 | t <sub>d(off)</sub>  | $R_G = 6.0 \Omega$                              |      | 108  |      | ns   |
| Fall Time                           | tf                   |   |      | 56   |      | ns   |
| Total Gate Charge                   | Q <sub>G</sub>       | V <sub>DD</sub> = 15 V                          |      | 8.0  |      | nC   |
| Gate to Source Charge               | Qgs                  | V <sub>GS</sub> = 5.0 V                         |      | 2.7  |      | nC   |
| Gate to Drain Charge                | Q <sub>GD</sub>      | I <sub>D</sub> = 7.0 A                          |      | 3.4  |      | nC   |
| Body Diode Forward Voltage          | V <sub>F(S-D)</sub>  | I <sub>F</sub> = 7.0 A, V <sub>GS</sub> = 0 V   |      | 0.84 |      | V    |

#### **TEST CIRCUIT 1 SWITCHING TIME**

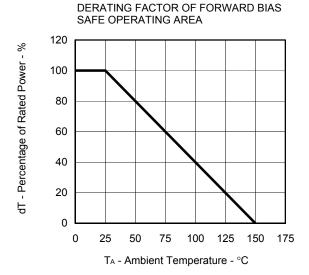
# PG. $\uparrow$ $R_{G}$ 0 $\tau = 1 \,\mu s$ Duty Cycle $\leq 1\%$



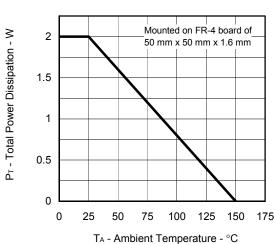
#### **TEST CIRCUIT 2 GATE CHARGE**



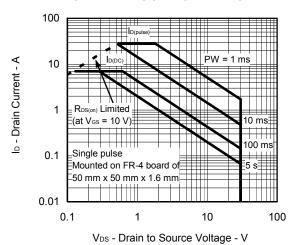
#### TYPICAL CHARACTERISTICS (TA = 25°C)



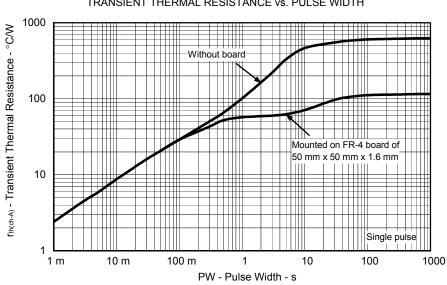
## TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



#### FORWARD BIAS SAFE OPERATING AREA

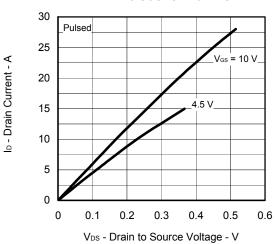


#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

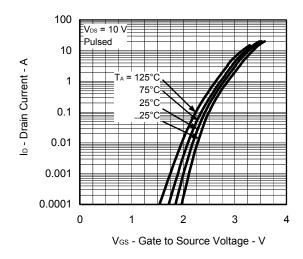


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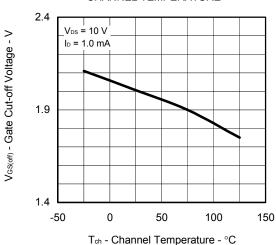
### DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



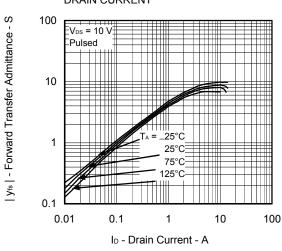
#### FORWARD TRANSFER CHARACTERISTICS



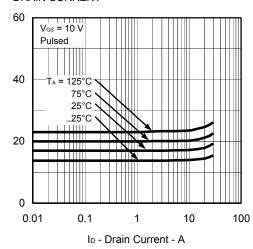
# GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



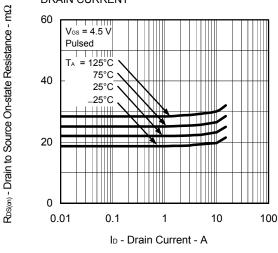
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



# DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



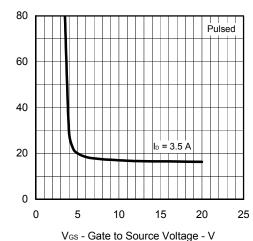
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



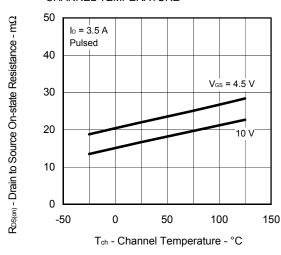
R<sub>DS(m)</sub> - Drain to Source On-state Resistance - mΩ

 $\mathsf{R}_{\mathsf{DS}(m)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

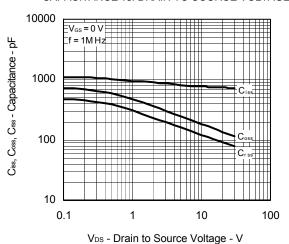
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



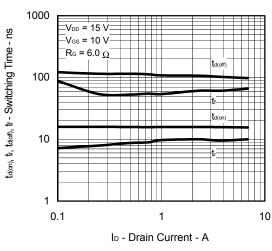
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



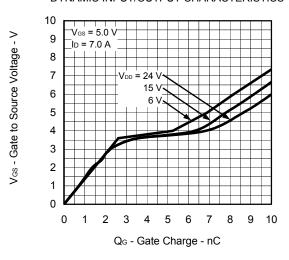
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



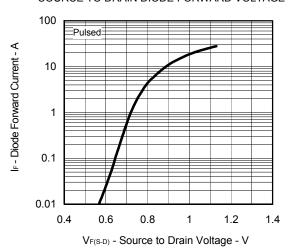
SWITCHING CHARACTERISTICS



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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